Preferred Devices

# Sensitive Gate Silicon Controlled Rectifiers

# **Reverse Blocking Thyristors**

Glassivated PNPN devices designed for high volume consumer applications such as temperature, light, and speed control; process and remote control, and warning systems where reliability of operation is important.

#### **Features**

- Pb-Free Packages are Available\*
- Glassivated Surface for Reliability and Uniformity
- Power Rated at Economical Prices
- Practical Level Triggering and Holding Characteristics
- Flat, Rugged, Thermopad Construction for Low Thermal Resistance, High Heat Dissipation and Durability
- Sensitive Gate Triggering
- Device Marking: Device Type, e.g., C106B, Date Code



## ON Semiconductor®

http://onsemi.com

SCRs 4 A RMS, 200 – 600 V

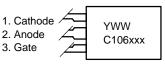




REAR VIEW SHOW TAB

TO-225AA CASE 077 STYLE 2

#### **MARKING DIAGRAM & PIN ASSIGNMENT**



 $xx = B, D, D1, D1G^*, M, MG^*, M1$ 

Y = Year WW = Work Week $G^* = Pb-Free$ 

## ORDERING INFORMATION

Device	Package	Shipping <sup>†</sup>
C106B	TO225AA	500/Box
C106D	TO225AA	500/Box
C106D1**	TO225AA	500/Box
C106D1G	TO225AA (Pb-Free)	500/Box
C106M	TO225AA	500/Box
C106MG	TO225AA (Pb-Free)	500/Box
C106M1**	TO225AA	500/Box

<sup>†</sup>For information on tape and reel specifications, including part orientation and tape sizes, please refer to our Tape and Reel Packaging Specifications Brochure, BRD8011/D.

**Preferred** devices are recommended choices for future use and best overall value.

<sup>\*\*</sup>D1 signifies European equivalent for D suffix and M1 signifies European equivalent for M suffix.

<sup>\*</sup>For additional information on our Pb–Free strategy and soldering details, please download the ON Semiconductor Soldering and Mounting Techniques Reference Manual, SOLDERRM/D.

#### MAXIMUM RATINGS (T<sub>J</sub> = 25°C unless otherwise noted)

Characteristic		Symbol	Max	Unit
Peak Repetitive Off–State Voltage (Note 1) (Sine Wave, 50–60 Hz, $R_{GK}$ = 1 k $\Omega$ , $T_{C}$ = -40° to 110°C)		V <sub>DRM,</sub> V <sub>RRM</sub>		V
	C106B C106D, C106D1* C106M, C106M1*		200 400 600	
On-State RMS Current (180° Conduction Angles, T <sub>C</sub> = 80°C)		I <sub>T(RMS)</sub>	4.0	А
Average On–State Current (180° Conduction Angles, T <sub>C</sub> = 80°C)		I <sub>T(AV)</sub>	2.55	А
Peak Non-Repetitive Surge Current (1/2 Cycle, Sine Wave, 60 Hz, T <sub>J</sub> = +110°C)		I <sub>TSM</sub>	20	А
Circuit Fusing Considerations (t = 8.3 ms)		l <sup>2</sup> t	1.65	A <sup>2</sup> s
Forward Peak Gate Power (Pulse Width ≤ 1.0 µsec, T <sub>C</sub> = 80°C)		P <sub>GM</sub>	0.5	W
Forward Average Gate Power (Pulse Width ≤ 1.0 µsec, T <sub>C</sub> = 80°C)		P <sub>G(AV)</sub>	0.1	W
Forward Peak Gate Current (Pulse Width ≤ 1.0 µsec, T <sub>C</sub> = 80°C)		I <sub>GM</sub>	0.2	А
Operating Junction Temperature Range		TJ	-40 to +110	°C
Storage Temperature Range		T <sub>stg</sub>	-40 to +150	°C
Mounting Torque (Note 2)		_	6.0	in. lb.

Maximum ratings are those values beyond which device damage can occur. Maximum ratings applied to the device are individual stress limit values (not normal operating conditions) and are not valid simultaneously. If these limits are exceeded, device functional operation is not implied, damage may occur and reliability may be affected.

## **THERMAL CHARACTERISTICS** ( $T_C = 25^{\circ}C$ unless otherwise noted.)

Characteristic		Max	Unit
Thermal Resistance, Junction to Case	$R_{\theta JC}$	3.0	°C/W
Thermal Resistance, Junction to Ambient	$R_{\theta JA}$	75	°C/W
Maximum Lead Temperature for Soldering Purposes 1/8" from Case for 10 Seconds		260	°C

<sup>\*</sup>D1 signifies European equivalent for D suffix and M1 signifies European equivalent for M suffix.

V<sub>DRM</sub> and V<sub>RRM</sub> for all types can be applied on a continuous basis. Ratings apply for zero or negative gate voltage; however, positive gate voltage shall not be applied concurrent with negative potential on the anode. Blocking voltages shall not be tested with a constant current source such that the voltage ratings of the devices are exceeded.

<sup>2.</sup> Torque rating applies with use of compression washer (B52200F006). Mounting torque in excess of 6 in. lb. does not appreciably lower case-to-sink thermal resistance. Anode lead and heatsink contact pad are common.

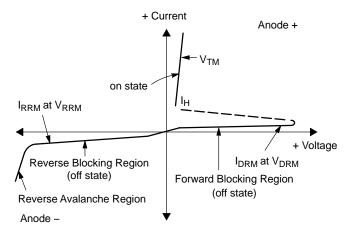
## **ELECTRICAL CHARACTERISTICS** ( $T_C = 25$ °C unless otherwise noted.)

Characteristic		Symbol	Min	Тур	Max	Unit
OFF CHARACTERISTICS		•	•	•	•	
Peak Repetitive Forward or Reverse Blocking Current ( $V_{AK}$ = Rated $V_{DRM}$ or $V_{RRM}$ , $R_{GK}$ = 1000 Ohms)	T <sub>J</sub> = 25°C T <sub>J</sub> = 110°C	I <sub>DRM</sub> , I <sub>RRM</sub>	_ _	_ _	10 100	μ <b>Α</b> μ <b>Α</b>
ON CHARACTERISTICS						
Peak Forward On–State Voltage (Note 3) (I <sub>TM</sub> = 4 A)		V <sub>TM</sub>	-	_	2.2	Volts
Gate Trigger Current (Continuous dc) (Note 4) (V <sub>AK</sub> = 6 Vdc, R <sub>L</sub> = 100 Ohms)	$T_J = 25$ °C $T_J = -40$ °C	I <sub>GT</sub>	_ _	15 35	200 500	μΑ
Peak Reverse Gate Voltage (I <sub>GR</sub> = 10 μA)		$V_{GRM}$	_	_	6.0	Volts
Gate Trigger Voltage (Continuous dc) (Note 4) (V <sub>AK</sub> = 6 Vdc, R <sub>L</sub> = 100 Ohms)	$T_{J} = 25^{\circ}C$ $T_{J} = -40^{\circ}C$	V <sub>GT</sub>	0.4 0.5	0.60 0.75	0.8 1.0	Volts
Gate Non–Trigger Voltage (Continuous dc) (Note 4) $(V_{AK} = 12 \text{ V}, R_L = 100 \text{ Ohms}, T_J = 110^{\circ}\text{C})$		$V_{\sf GD}$	0.2	_	-	Volts
Latching Current (V <sub>AK</sub> = 12 V, I <sub>G</sub> = 20 mA)	T <sub>J</sub> = 25°C T <sub>J</sub> = -40°C	IL.	_ _	0.20 0.35	5.0 7.0	mA
Holding Current (V <sub>D</sub> = 12 Vdc) (Initiating Current = 20 mA, Gate Open)	$T_J = 25^{\circ}C$ $T_J = -40^{\circ}C$ $T_J = +110^{\circ}C$	lн	_ _ _	0.19 0.33 0.07	3.0 6.0 2.0	mA
DYNAMIC CHARACTERISTICS						
Critical Rate-of-Rise of Off-State Voltage (V <sub>AK</sub> = Rated V <sub>DRM</sub> , Exponential Waveform, R <sub>GK</sub> = 10 T <sub>J</sub> = 110°C)	00 Ohms,	dv/dt	_	8.0	_	V/µs

Pulse Test: Pulse Width ≤ 2.0 ms, Duty Cycle ≤ 2%.
 R<sub>GK</sub> is not included in measurement.

## **Voltage Current Characteristic of SCR**

Symbol	Parameter
$V_{DRM}$	Peak Repetitive Off State Forward Voltage
I <sub>DRM</sub>	Peak Forward Blocking Current
$V_{RRM}$	Peak Repetitive Off State Reverse Voltage
I <sub>RRM</sub>	Peak Reverse Blocking Current
$V_{TM}$	Peak On State Voltage
I <sub>H</sub>	Holding Current



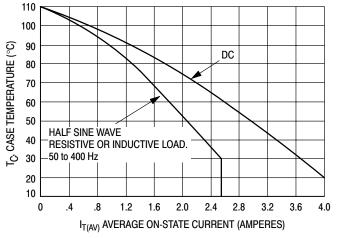


Figure 1. Average Current Derating

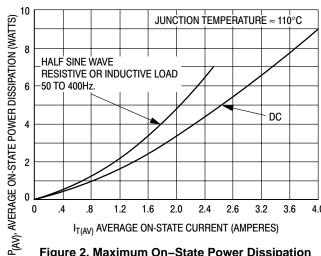


Figure 2. Maximum On-State Power Dissipation

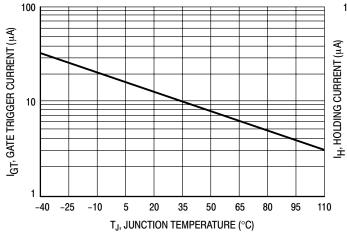


Figure 3. Typical Gate Trigger Current versus **Junction Temperature** 

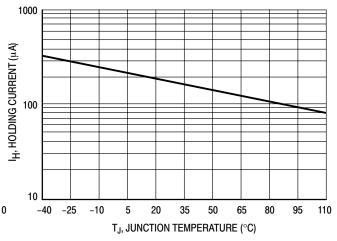


Figure 4. Typical Holding Current versus **Junction Temperature** 

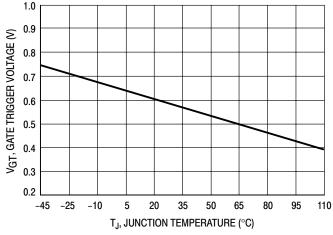


Figure 5. Typical Gate Trigger Voltage versus **Junction Temperature** 

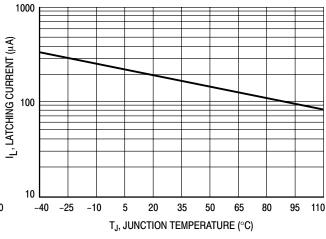
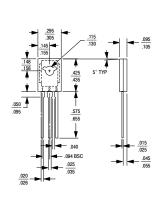


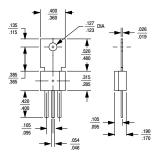
Figure 6. Typical Latching Current versus **Junction Temperature** 

## Package Interchangeability

The dimensional diagrams below compare the critical dimensions of the ON Semiconductor C-106 package with competitive devices. It has been demonstrated that the smaller dimensions of the ON Semiconductor package make it compatible in most lead-mount and chassis-mount applications. The user is advised to compare all critical dimensions for mounting compatibility.



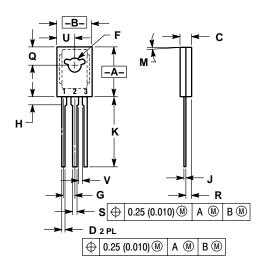
**ON Semiconductor C-106 Package** 



**Competitive C-106 Package** 

#### PACKAGE DIMENSIONS

TO-225AA (formerly TO-126) CASE 077-09 ISSUE Z



#### NOTES:

- DIMENSIONING AND TOLERANCING PER ANSI Y14.5M, 1982.
- 2. CONTROLLING DIMENSION: INCH.
  3. 077-01 THRU -08 OBSOLETE, NEW STANDARD

	INCHES		MILLIMETERS	
DIM	MIN	MAX	MIN	MAX
Α	0.425	0.435	10.80	11.04
В	0.295	0.305	7.50	7.74
С	0.095	0.105	2.42	2.66
D	0.020	0.026	0.51	0.66
F	0.115	0.130	2.93	3.30
G	0.094 BSC		2.39 BSC	
Н	0.050	0.095	1.27	2.41
J	0.015	0.025	0.39	0.63
K	0.575	0.655	14.61	16.63
M	5° TYP		5°	TYP
Q	0.148	0.158	3.76	4.01
R	0.045	0.065	1.15	1.65
S	0.025	0.035	0.64	0.88
U	0.145	0.155	3.69	3.93
V	0.040		1.02	

STYLE 2:

PIN 1. CATHODE

- ANODE
- 2. 3. GATE

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